

Low voltage high performance PNP power transistors

Preliminary Data

Features

- Very low collector-emitter saturation voltage
- High current gain characteristic
- Fast switching speed
- Surface mounting devices in medium power SOT-89 and SOT-223 packages

Applications

- Emergency lighting
- LED
- Motherboard and hard disk drive
- Mobile equipment
- Battery charger
- Voltage regulation

Description

The 2STF2550 and 2STN2550 are PNP transistors manufactured using new "PB-HCD" (Power bipolar high current density) technology. The resulting transistor shows exceptional high gain performances coupled with very low saturation voltage.

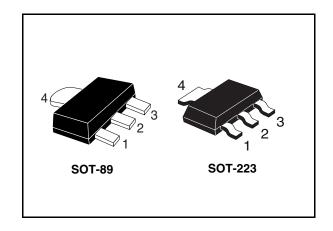


Figure 1. Internal schematic diagram

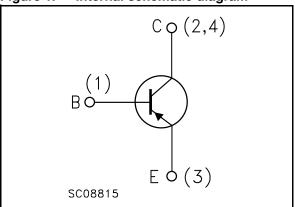


Table 1. Device summary

Order codes	Marking	Package	Packaging
2STF2550	2550	SOT-89	Tape and reel
2STN2550	N2550	SOT-223	iape and reei

Electrical ratings 2STF2550 - 2STN2550

1 Electrical ratings

Table 2. Absolute maximum rating

		Va		
Symbol	Parameter	2STF2550 2STN2550		Unit
		SOT-89	SOT-223	
V _{CES}	Collector-emitter voltage ($V_{CE} = 0$)	lector-emitter voltage (V _{CE} = 0) -50		V
V _{CEO}	Collector-emitter voltage (I _B = 0) -50		V	
V _{EBO}	Emitter-base voltage ($I_C = 0$)	-5		V
I _C	Collector current -5		Α	
I _{CM}	Collector peak current (t _P < 5 ms)	-10		Α
I _B	Base current	current -1		Α
P _{TOT}	Total dissipation at T _{amb} = 25 °C 1.4 1.6		W	
T _{stg}	Storage temperature -65 to 150		°C	
TJ	Max. operating junction temperature 150		°C	

Table 3. Thermal data

Symbol	Parameter	SOT-89	SOT-223	Unit
R _{thj-amb} ⁽¹⁾	Thermal resistance junction-amb max	89	78	°C/W

^{1.} Device mounted on PCB area of 1 cm²

2 Electrical characteristics

 $(T_{case} = 25 \, ^{\circ}C \text{ unless otherwise specified})$

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector cut-off current (I _E = 0)	V _{CB} = -50 V			-0.1	μА
I _{EBO}	Emitter cut-off current (I _C = 0)	V _{EB} = -4 V			-0.1	μА
V _{(BR)CBO}	Collector-base breakdown voltage (I _E = 0)	I _C = -100 μA	-50			V
V _{(BR)CEO} (1)	Collector-emitter breakdown voltage (I _B = 0)	I _C = -10 mA	-50			٧
V _{(BR)EBO}	Emitter-base breakdown voltage ($I_C = 0$)	I _E = -100 μA	-5			V
h _{FE} ⁽¹⁾	DC current gain	$\begin{split} I_{C} &= -0.5 \text{ A} & V_{CE} &= -2 \text{ V} \\ I_{C} &= -2 \text{ A} & V_{CE} &= -2 \text{ V} \\ I_{C} &= -3 \text{ A} & V_{CE} &= -2 \text{ V} \\ I_{C} &= -5 \text{ A} & V_{CE} &= -5 \text{ V} \end{split}$	110 80	350 70	350	
V _{CE(sat)} (1)	Collector-emitter saturation voltage	$I_C = -3 \text{ A}$ $I_B = -300 \text{ mA}$		-0.39	-0.55	V
V _{BE(sat)} (1)	Base-emitter saturation voltage	$I_C = -3 \text{ A}$ $I_B = -300 \text{ mA}$		-1	-1.2	>
C _{CBO}	Collector-base capacitance (I _E = 0)	V _{CB} = -10 V, f = 1 MHz		30		pF
t _{on} t _{off}	Resistive load Turn-on time Turn-off time	$I_C = -1.5 \text{ A}$ $V_{CC} = -10 \text{ V}$ $I_{B1} = -I_{B2} = -150 \text{ mA}$		80 3 00		ns ns

^{1.} Pulsed duration = 300 μ s, duty cycle \leq 1.5%

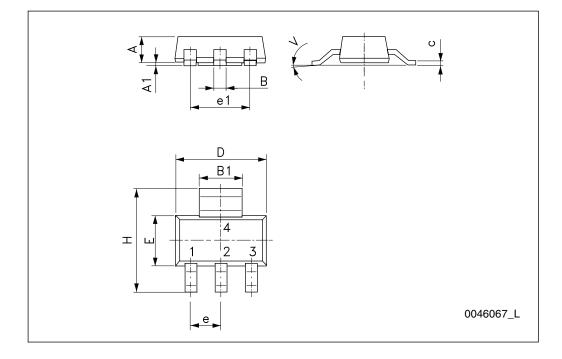
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3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

SOT-223 mechanical data

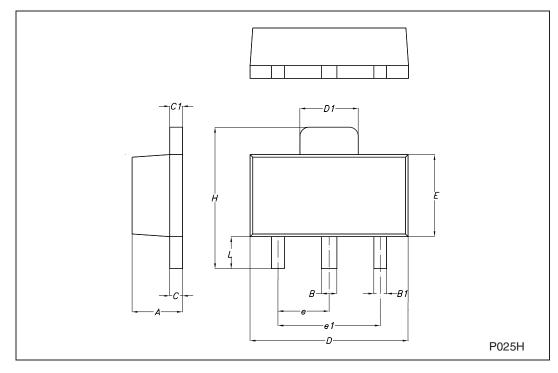
DIM.	mm.					
DIW.	min.	typ	max.			
Α			1.80			
A1	0.02		0.1			
В	0.60	0.70	0.85			
B1	2.90	3.00	3.15			
С	0.24	0.26	0.35			
D	6.30	6.50	6.70			
е		2.30				
e1		4.60				
E	3.30	3.50	3.70			
Н	6.70	7.00	7.30			
V			10 °			



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SOT-89 MECHANICAL DATA

DIM.		mm				
Dim.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α	1.4		1.6	55.1		63.0
В	0.44		0.56	17.3		22.0
B1	0.36		0.48	14.2		18.9
С	0.35		0.44	13.8		17.3
C1	0.35		0.44	13.8		17.3
D	4.4		4.6	173.2		181.1
D1	1.62		1.83	63.8		72.0
E	2.29		2.6	90.2		102.4
е	1.42		1.57	55.9		61.8
e1	2.92		3.07	115.0		120.9
Н	3.94		4.25	155.1		167.3
L	0.89		1.2	35.0		47.2



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2STF2550 - 2STN2550 Revision history

4 Revision history

Table 5. Document revision history

Date	Revision	Changes
12-Nov-2008	1	Initial release

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